

Property	Specification
Material	Multicrystalline UMG Silicon
Type	P-type (Boron doped)
Resistivity	0.3 - 3 ohm-cm
Brick Lifetime	>1.5us
Wafer Dimensions (W)	156(±0.5)*156(±0.5)mm
Squareness	90±0.5 degree
Thickness	200um +/-30 um center 1 point check
Chamfering Bevel Edge Width	1mm - 2mm
T T V	≤50um 5 points check
Saw Mark (Rt)	≤20um
Bump/Step	≤30um
Edge Defects	No V-type sharp chip (Not seen by naked eyes)
	No crack
	Q'ty of Rounded chips≤2 Depth≤1.0 mm, Length≤1.5mm
Appearance	As-cut, cleaned, no visible stain, no pits
	Warpage Height<150um
	No remarkable water mark
Crystal grain	Crystal grain ≤2x2cm ² ; 1x1cm ² more than 10 grain = NG
Impurities	Not seen by naked eyes (no pin hold)
B grade spec.	T = +60/-40 um center 1 point check TTV≤50um 5 point check